MICROWAVE POWER GaAs FET TIM0910-30L

MICROWAVE SEMICONDUCTOR TECHNICAL DATA

FEATURES

- ·BROAD BAND INTERNALLY MATCHED FET ·HIGH POWER
- P1dB= 45.0dBm at 9.5GHz to 10.5GHz

HIGH GAIN

G1dB= 7.0dB at 10.5GHz to 10.5GHz

·LOW INTERMODULATION DISTORTION

IM3= -25dBc (Min.) at Pout= 38dBm (Single Carrier Level)

·HERMETICALLY SEALED PACKAGE



CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.	
Output Power at 1dB Gain Compression Point	P1dB	VDS= 10V IDSset= 7.0A f= 9.5 to 10.5GHz Two-Tone Test Po= 38dBm, ∆f= 5MHz (Single Carrier Level)	dBm	44.0	45.0		
Power Gain at 1dB Gain Compression Point	G1dB		dB	6.0	7.0		
Drain Current	IDS1		А		10.0	11.5	
Gain Flatness	ΔG		dB			±0.8	
Power Added Efficiency	ηadd		%		25		
3rd Order Intermodulation Distortion	IM3		dBc	-25		_	
Drain Current	IDS2		А		9.0	10.1	
Channel Temperature Rise	∆Tch	(VDS × IDS + Pin – P1dB) × Rth(c-c)	°C			100	

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

Recommended Gate Resistance (Rg): 10 Ω

ELECTRICAL CHARACTERISTICS (Ta= 25°C)

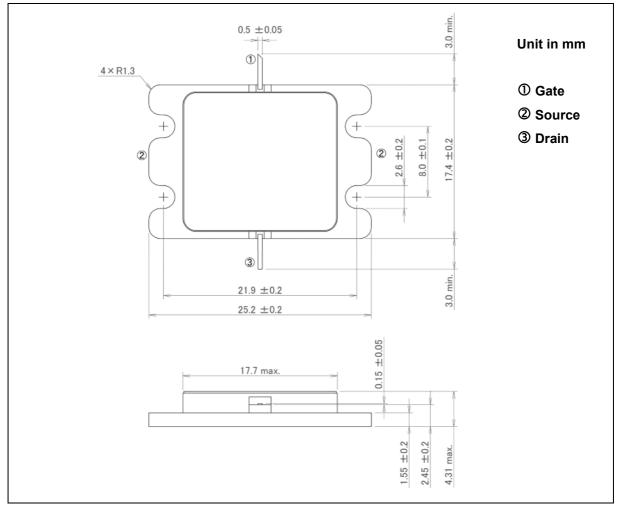
CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 3V IDS= 9.6A	S	_	5.5	_
Pinch-off Voltage	VGSoff	VDS= 3V IDS= 290mA	V	-0.7	-2.0	-4.5
Saturated Drain Current	IDSS	VDS= 3V VGS= 0V	А		20.0	
Gate-Source Breakdown Voltage	VGSO	IGS= -290µA	V	-5		
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W		1.0	1.1

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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	VDS	V	15
Gate-Source Voltage	VGS	V	-5
Drain Current	IDS	А	20
Total Power Dissipation (Tc= 25°C)	PT	W	136
Channel Temperature	Tch	°C	175
Storage	Tstg	°C	-65 to +175

PACKAGE OUTLINE (7-AA03B)



HANDLING PRECAUTIONS FOR PACKAGE MODEL

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C or 3 seconds at 350°C.

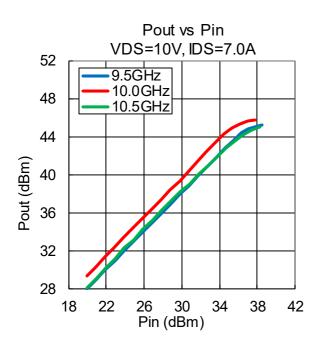
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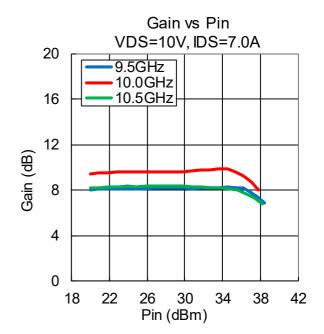
TYPICAL RF PERFORMANCE

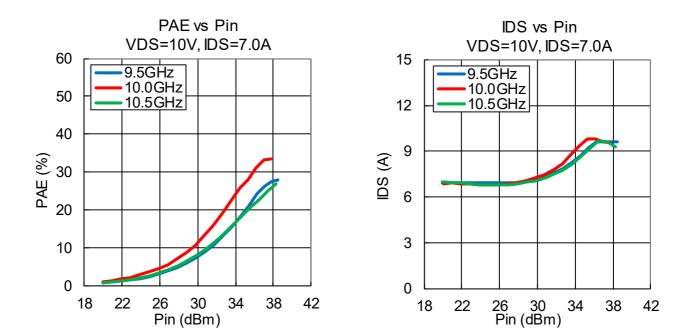
ROWAVE SEMICONDUCTOR TECHNICAL DATA

·Pout , Gain , PAE , IDS vs. Pin

VDS= 10 V, IDSset= 7.0 A, f= 9.5, 10.0, 10.5 GHz, Ta= +25 °C





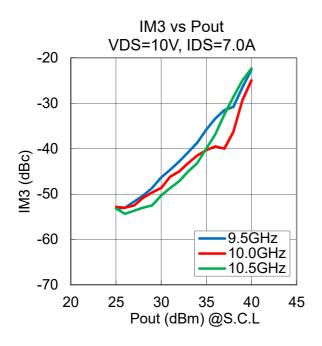


MICROWAVE SEMICONDUCTOR TECHNICAL DATA

MICROWAVE POWER GaAs FET TIM0910-30L

·IM3 vs. Pout

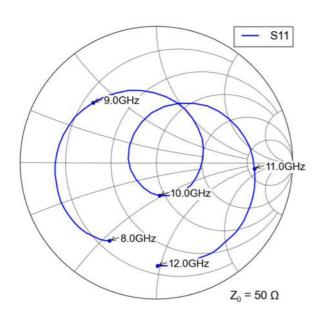
VDS= 10 V, IDSset= 7.0 A, f= 9.5, 10.0, 10.5 GHz, Δf = 5 MHz , Ta= +25 $\,\,^\circ \! C$

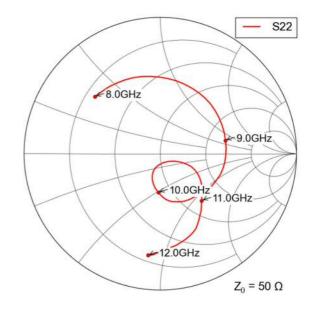


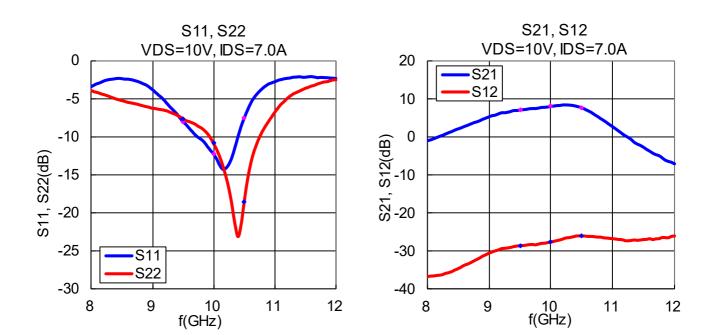
MICROWAVE SEMICONDUCTOR TECHNICAL DATA

·S-Parameters

VDS= 10 V, IDSset= 7.0 A, f= 8.0 to 12.0 GHz, Ta= +25 °C







MICROWAVE SEMICONDUCTOR TECHNICAL DATA

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